

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI OSC-0.7L** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	500 mA
V_{CB}	40 V
P_{DISS}	7.0 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	25 °C/W

PACKAGE STYLE TO-46

DIM	MINIMUM inches/mm	MAXIMUM inches/mm
A	.100 / 2.540	
B	.028 / 0.710	.048 / 1.220
C	.035 / 0.890	.046 / 1.170
D	.209 / 5.310	.229 / 5.840
E	.178 / 4.520	.195 / 4.950
F	.065 / 1.650	.085 / 2.160
G	.500 / 12.700	
H	.012 / 0.3050	.019 / 0.4830

ORDER CODE: ASI10637

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 1.0 mA			20			V
BV_{CBO}	I _C = 100 μA			40			V
BV_{EBO}	I _E = 100 μA			3.0			V
I_{CBO}	V _{CB} = 18 V					100	μA
h_{FE}	V _{CE} = 5.0 V	I _C = 100 mA		25		250	---
C_{OB}	V _{CB} = 18 V	f = 1.0 MHz				5.0	pF
η_C	V _{CC} = 18 V	P _{OUT} = 0.7 W	f = 1.68 GHz		25		%
f_t	V _{CE} = 10 V	I _E = 100 mA	f = 200 MHz		2500		MHz
P_{OSC}	V _{CC} = 18 V	I _E = 150 mA	f = 1.68 GHz		700		mW